

BC212,B,C TRANSISTOR(PNP)

FEATURES

Power dissipation

P_{CM} : 0.35W ($T_{amb}=25^{\circ}C$)

Collector current

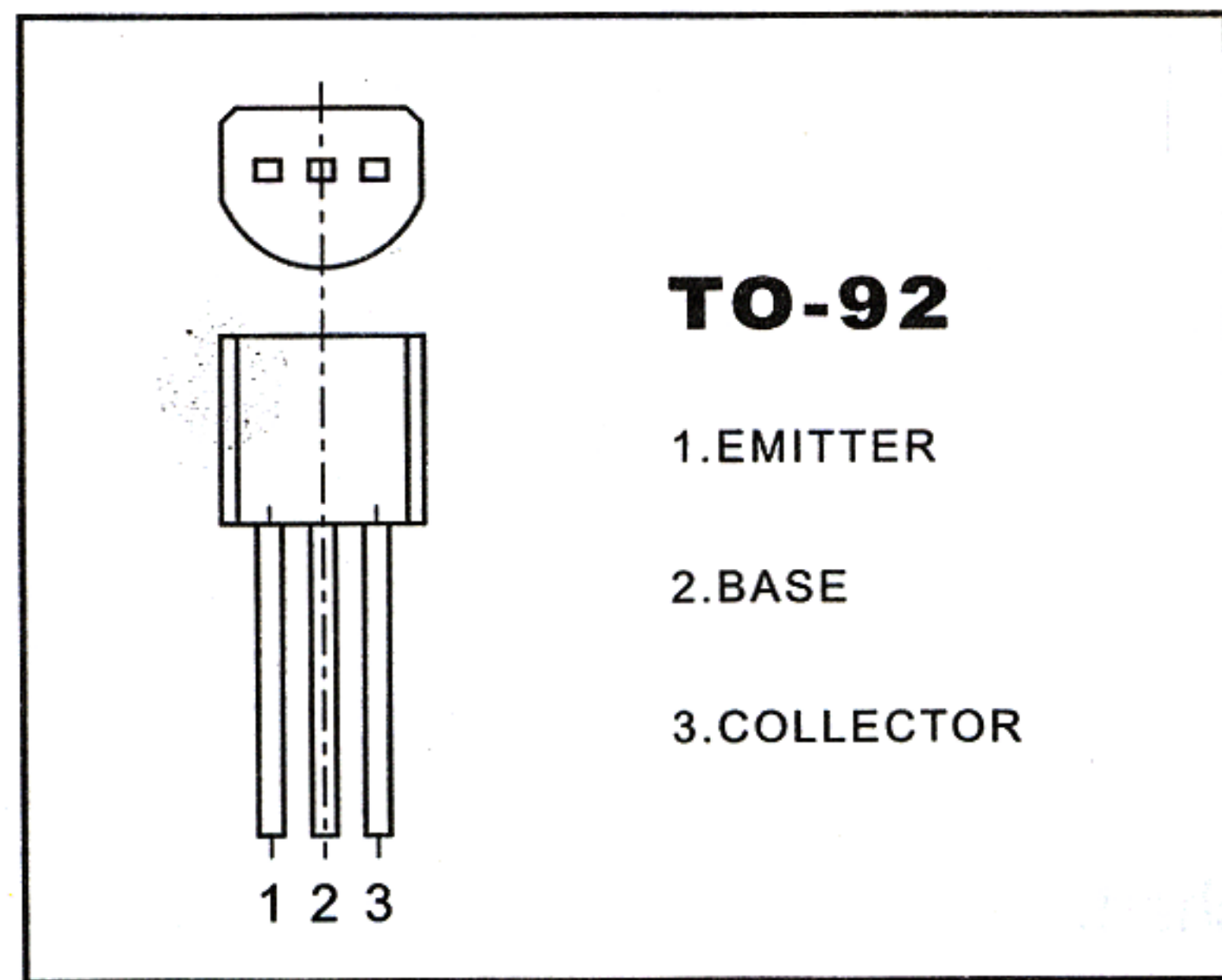
I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -60V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu A, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2 mA, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30 V, I_E = 0$		-15	nA
Collector cut-off current	I_{CEO}	$V_{CE} = -30V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 V, I_C = 0$		-15	nA
DC current gain	BC212	$V_{CE} = -5 V, I_C = -2 mA$	140	600	
	BC212B		140	400	
	BC212C		350	600	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100 mA, I_B = -5 mA$		-0.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -100 mA, I_B = -5 mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -5 V, I_C = -10 mA$ $f = 100MHz$	200		MHz